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C1
sacrificial etch portion simultaneously, said first surface of said sacrificial etch portion being formed of a substantially pure metallic material capable of being etched by said plasma and configured to be parallel with said first surface of said semiconductor substrate;

positioning said semiconductor substrate and said sacrificial substrate holder into said plasma processing chamber;

striking said plasma from an etchant source gas released into said plasma processing chamber; and

simultaneously etching said first surface of said semiconductor substrate and said first surface of said sacrificial etch portion using said plasma.

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4. (Once Amended) The method of claim 1 wherein said etching is a metallization etch, said substantially pure metallic material comprising substantially pure aluminum.

25[11].(Once Amended) In a plasma processing chamber, a method for improving etch uniformity while etching a semiconductor substrate, comprising:

providing an annular sacrificial substrate holder having a substantially pure metallic planar upper surface;

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placing a semiconductor substrate within said sacrificial substrate holder such that an upper surface of said semiconductor substrate is substantially even with said planar upper surface of said annular sacrificial substrate holder; and

creating a plasma etching cloud from an etchant source gas released into said plasma processing chamber to simultaneously etch said upper surface of said semiconductor substrate and upper planar surface of said sacrificial etch portion, wherein said sacrificial substrate holder is dimensioned such that said plasma etching cloud extends beyond an outer periphery of said sacrificial substrate holder during said etching.

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26[12]. (Once Amended) The method of claim [11] 25 wherein said etching is an aluminum etch and wherein the substantially pure metallic planar upper surface is a substantially pure aluminum planar upper surface.

27[13]. (Once Amended) The method of claim [12] 26 wherein said etchant source gas includes chlorine.

28[14]. (Once Amended) The method of claim [13] 27 wherein said plasma processing chamber represents an inductively coupled plasma processing chamber.

29[15]. (Once Amended) The method of claim [11] 25 wherein said plasma processing chamber represents an inductively coupled plasma processing chamber.

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30[16]. (Once Amended) The method of claim [11] 25 wherein said plasma processing chamber represents a transformer coupled plasma processing chamber.

31[17]. (Once Amended) The method of claim [11] 25 wherein a lower surface of said semiconductor substrate is in direct contact with a chuck of said plasma processing chamber.

32[18]. (Once Amended) The method of claim [17] 31 wherein said chuck represents a chuck employing helium cooling.

33[19]. (Once Amended) The method of claim [11] 25 wherein an inner periphery of said annular sacrificial substrate holder is dimensioned to [snugly fit] contact said semiconductor substrate.